



SANYO Semiconductors
DATA SHEET

2SC6096 — NPN Epitaxial Planar Silicon Transistor

High-Voltage Switching Applications

Applications

- DC / DC converter, relay drivers, lamp drivers, motor drivers, inverter.

Features

- Adoption of FBET, MBIT process.
- High current capacitance.
- Low collector-to-emitter saturation voltage.
- High-speed switching.
- High allowable power dissipation.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings		Unit
Collector-to-Base Voltage	V _{CBO}		120		V
Collector-to-Emitter Voltage	V _{CES}		120		V
Collector-to-Emitter Voltage	V _{CEO}		100		V
Emitter-to-Base Voltage	V _{EBO}		6.5		V
Collector Current	I _C		2		A
Collector Current (Pulse)	I _{CP}		3		A
Base Current	I _B		400		mA
Collector Dissipation	P _C	Mounted on a ceramic board (250mm ² ×0.8mm)	1.3		W
		T _c =25°C	3.5		W
Junction Temperature	T _j		150		°C
Storage Temperature	T _{stg}		-55 to +150		°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	I _{CBO}	V _{CB} =80V, I _E =0A			1	μA
Emitter Cutoff Current	I _{EBO}	V _{EB} =4V, I _C =0A			1	μA
DC Current Gain	h _{FE}	V _{CE} =5V, I _C =100mA	300		600	

Marking : QG

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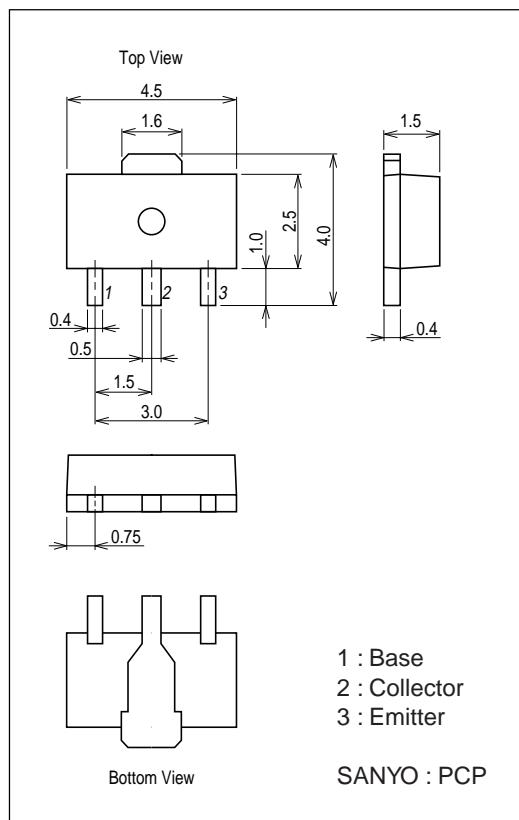
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Parameter	Symbol	Conditions	Ratings			Unit	
			min	typ	max		
Gain-Bandwidth Product	f_T	$V_{CE}=10V, I_C=300mA$			300	MHz	
Output Capacitance	C_{OB}	$V_{CB}=10V, f=1MHz$			13	pF	
Collector-to-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=1A, I_B=100mA$			100	150	mV
Base-to-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=1A, I_B=100mA$			0.85	1.2	V
Collector-to-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C=10\mu A, I_E=0A$	120			V	
Collector-to-Emitter Breakdown Voltage	$V_{(BR)CES}$	$I_C=100\mu A, R_{BE}=0\Omega$	120			V	
Collector-to-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=1mA, R_{BE}=\infty$	100			V	
Emitter-to-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=10\mu A, I_C=0A$	6.5			V	
Turn-ON Time	t_{on}	See specified Test Circuit.			40	ns	
Storage Time	t_{stg}	See specified Test Circuit.			1100	ns	
Fall Time	t_f	See specified Test Circuit.			40	ns	

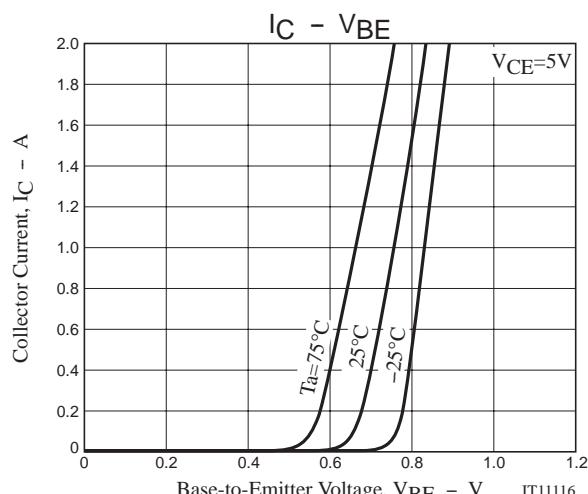
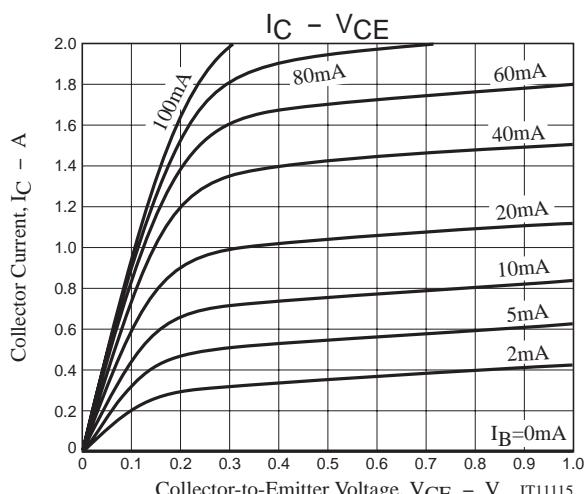
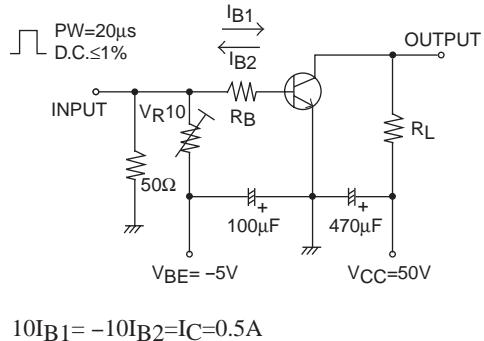
Package Dimensions

unit : mm

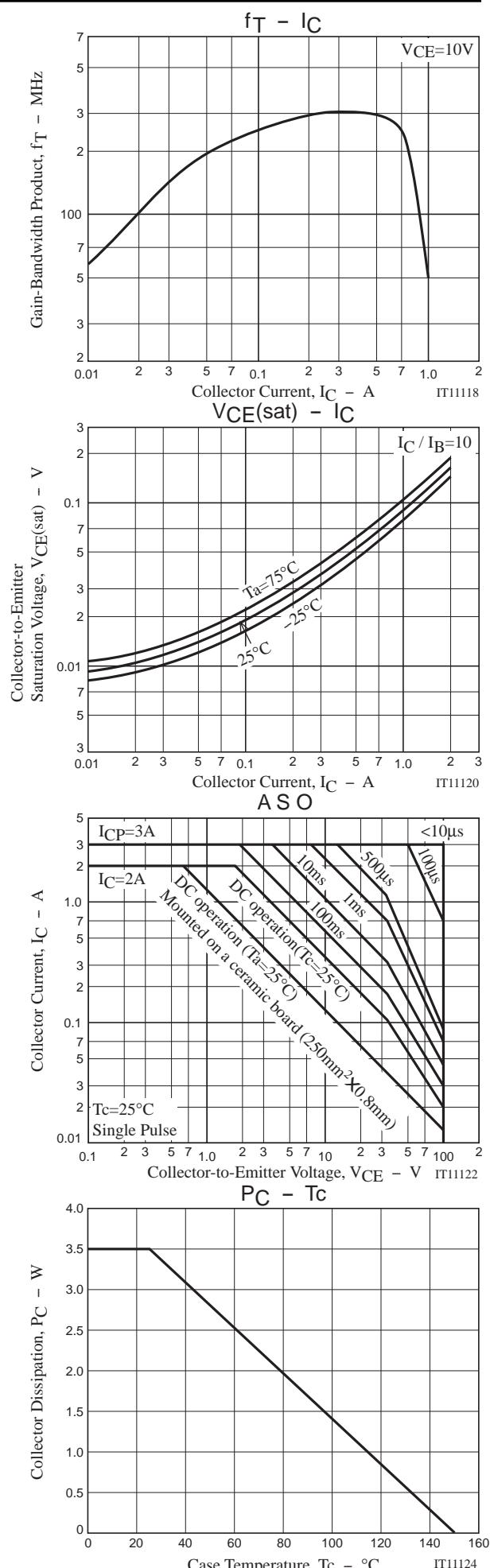
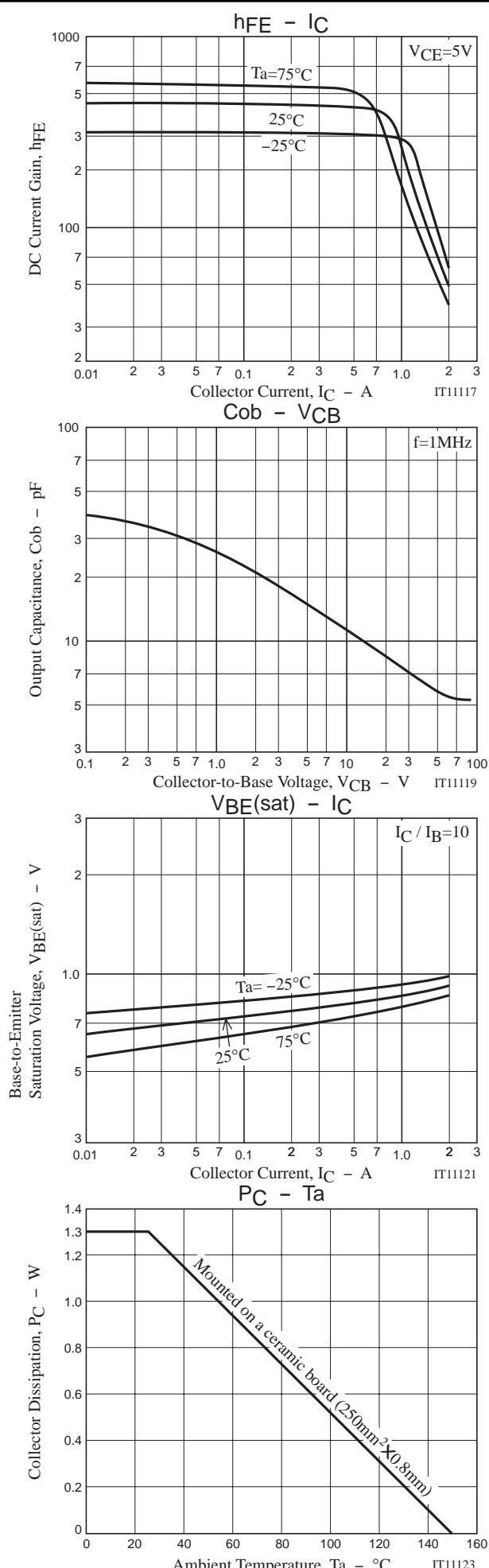
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Switching Time Test Circuit



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